

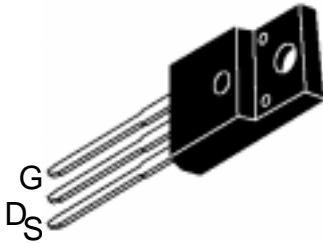


IRF640FP 18A 200V N CHANNEL POWER MOSFET

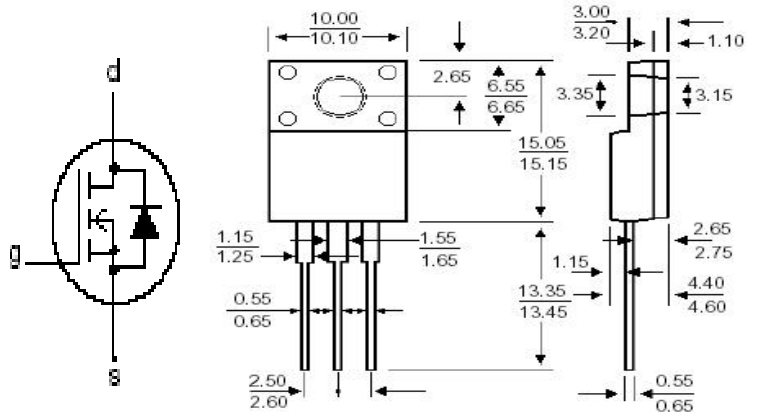
Description

Mechanical Dimensions

IRF640FP



ITO-220AB



GENERAL DESCRIPTION

This Power MOSFET is designed for low voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.

FEATURES

- ◆ Silicon Gate for Fast Switching Speeds
- ◆ Low $R_{DS(on)}$ to Minimize On-Losses. Specified at Elevated Temperature
- ◆ Rugged – SOA is Power Dissipation Limited
- ◆ Source-to-Drain Characterized for Use With Inductive Loads

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain to Current – Continuous	I_D	18	A
– Pulsed	I_{DM}	72	
Gate-to-Source Voltage – Continue	V_{GS}	± 20	V
– Non-repetitive	V_{GSM}	± 40	V
Total Power Dissipation	P_D	125	W
Derate above 25°C		1.00	W/°C
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C
Single Pulse Drain-to-Source Avalanche Energy – $T_J = 25^\circ\text{C}$ ($V_{DD} = 100\text{V}, V_{GS} = 10\text{V}, I_L = 18\text{A}, L = 1.38\text{mH}, R_G = 25\Omega$)	E_{AS}	224	mJ
Thermal Resistance – Junction to Case	θ_{JC}	1.00	°C/W
– Junction to Ambient	θ_{JA}	62.5	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	°C

(1) Pulse Width and frequency is limited by $T_J(\text{max})$ and thermal response



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ELECTRICAL CHARACTERISTICS

Unless otherwise specified, $T_J = 25^\circ\text{C}$.

Characteristic	Symbol	IRF640			Units
		Min	Typ	Max	
Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ V}$, $I_D = 250\ \mu\text{A}$)	$V_{(BR)DSS}$	200			V
Drain-Source Leakage Current ($V_{DS} = \text{Rated } V_{DSS}$, $V_{GS} = 0\text{ V}$) ($V_{DS} = 0.8\text{Rated } V_{DSS}$, $V_{GS} = 0\text{ V}$, $T_J = 125^\circ\text{C}$)	I_{DSS}			0.025 1.0	mA
Gate-Source Leakage Current-Forward ($V_{gsf} = 20\text{ V}$, $V_{DS} = 0\text{ V}$)	I_{GSSF}			100	nA
Gate-Source Leakage Current-Reverse ($V_{gsr} = 20\text{ V}$, $V_{DS} = 0\text{ V}$)	I_{GSSR}			100	nA
Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$)	$V_{GS(th)}$	2.0		4.0	V
Static Drain-Source On-Resistance ($V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$) *	$R_{DS(on)}$			0.18	Ω
Drain-Source On-Voltage ($V_{GS} = 10\text{ V}$) ($I_D = 5.0\text{ A}$)	$V_{DS(on)}$			6.0	V
Forward Transconductance ($V_{DS} = 50\text{ V}$, $I_D = 10\text{ A}$) *	g_{FS}	6.8			mhos
Input Capacitance	$(V_{DS} = 25\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{iss}		1600	pF
Output Capacitance		C_{oss}		750	pF
Reverse Transfer Capacitance		C_{rss}		300	pF
Turn-On Delay Time	$(V_{DD} = 30\text{ V}$, $I_D = 10\text{ A}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\Omega$) *	$t_{d(on)}$		30	ns
Rise Time		t_r		60	ns
Turn-Off Delay Time		$t_{d(off)}$		80	ns
Fall Time		t_f		60	ns
Total Gate Charge	$(V_{DS} = 0.8\text{Rated } V_{DSS}$, $I_D = \text{Rated } I_D$, $V_{GS} = 10\text{ V}$) *	Q_g	36	63	nC
Gate-Source Charge		Q_{gs}	16		nC
Gate-Drain Charge		Q_{gd}	26		nC
Internal Drain Inductance (Measured from the drain lead 0.25" from package to center of die)	L_D		4.5		nH
Internal Drain Inductance (Measured from the source lead 0.25" from package to source bond pad)	L_S		7.5		nH
SOURCE-DRAIN DIODE CHARACTERISTICS					
Forward On-Voltage(1)	$(I_S = \text{Rated } I_D$, $dI_S/dt = 100\text{A}/\mu\text{s}$)	V_{SD}		1.5	V
Forward Turn-On Time		t_{on}	**		ns
Reverse Recovery Time		t_{rr}		450	

* Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$

** Negligible, Dominated by circuit inductance



TYPICAL ELECTRICAL CHARACTERISTICS

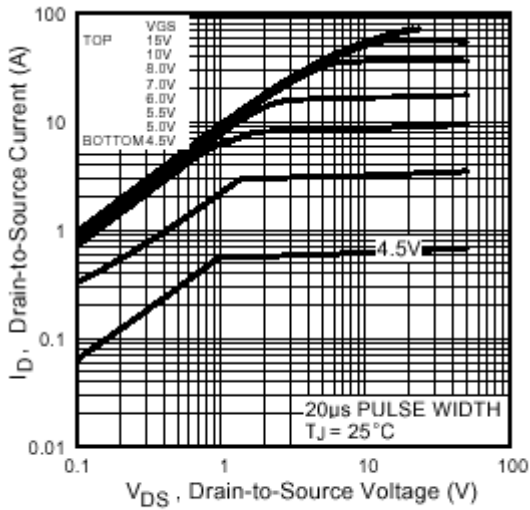


Fig 1. Typical Output Characteristics

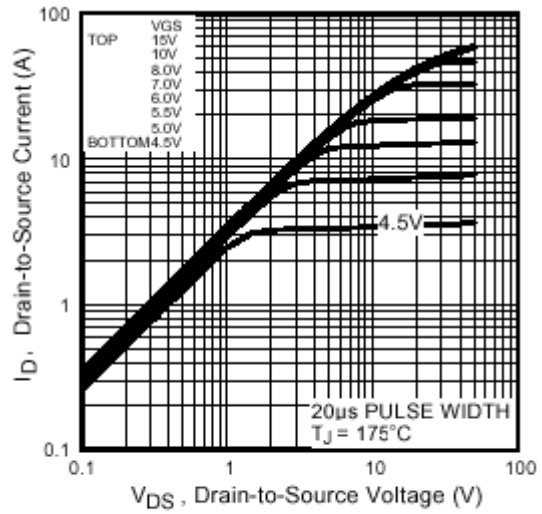


Fig 2. Typical Output Characteristics

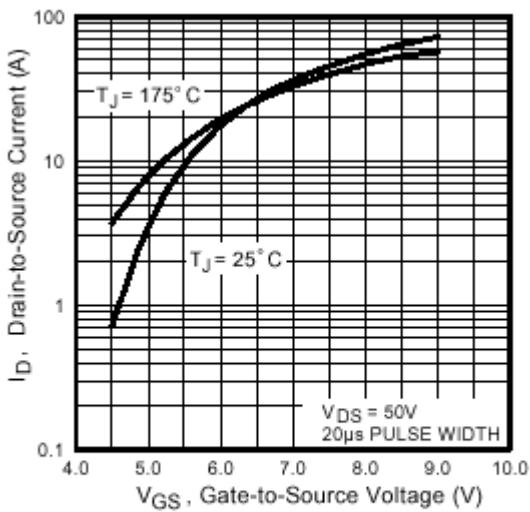


Fig 3. Typical Transfer Characteristics

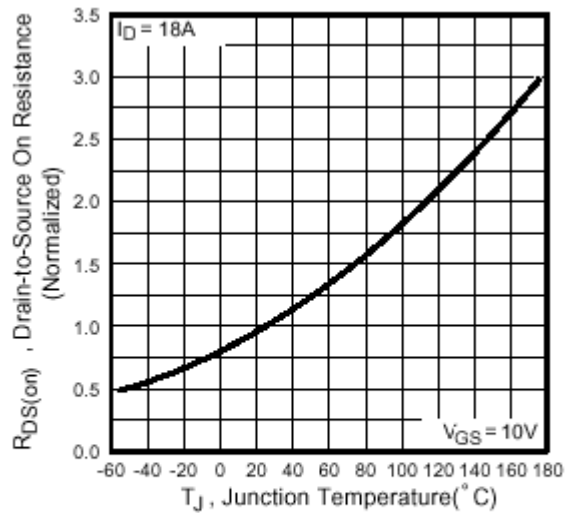


Fig 4. Normalized On-Resistance Vs. Temperature



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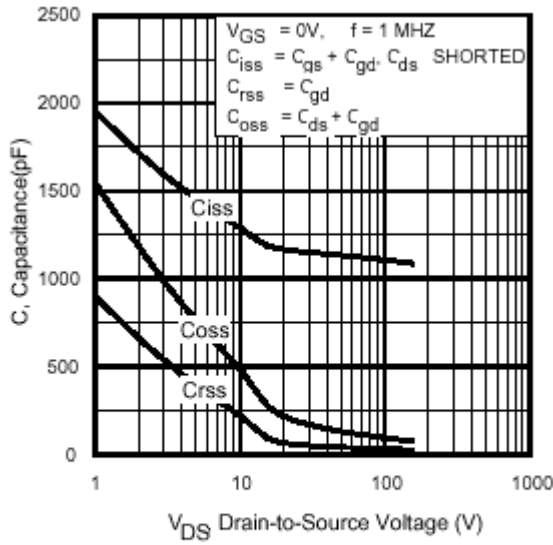


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

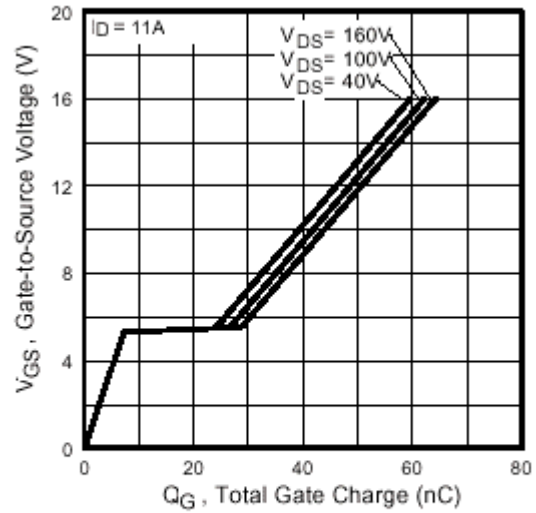


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

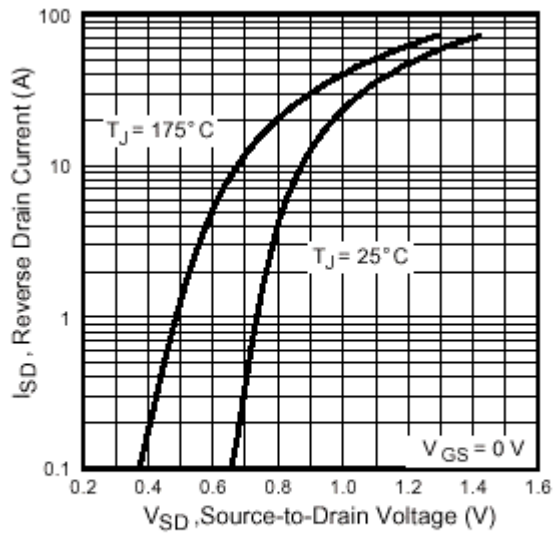


Fig 7. Typical Source-Drain Diode Forward Voltage

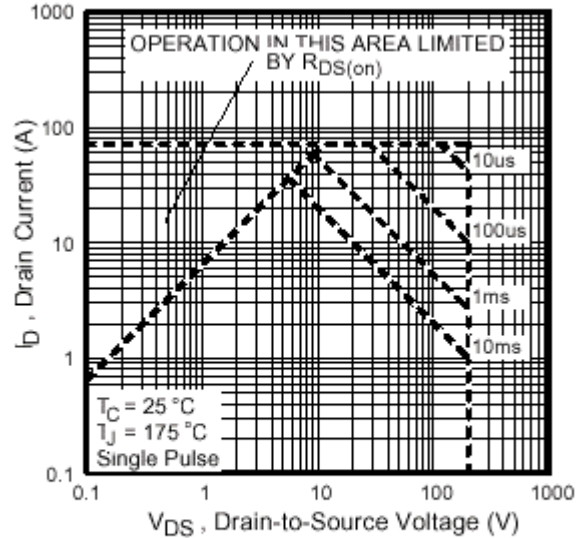


Fig 8. Maximum Safe Operating Area



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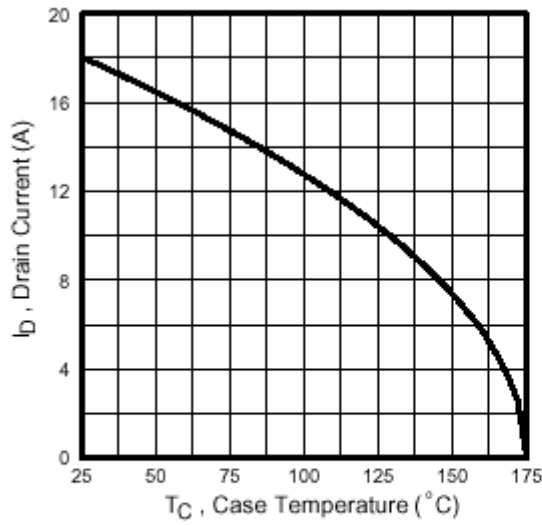


Fig 9. Maximum Drain Current Vs. Case Temperature

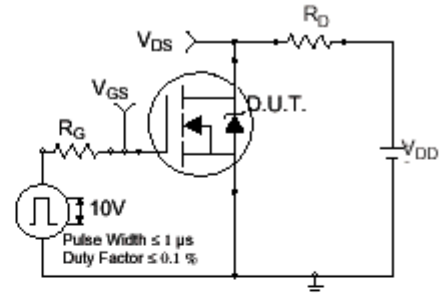


Fig 10a. Switching Time Test Circuit

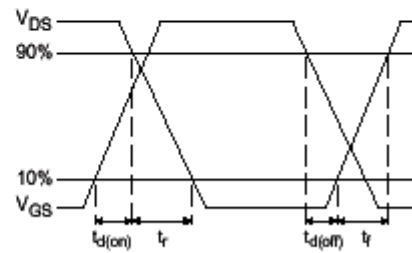


Fig 10b. Switching Time Waveforms

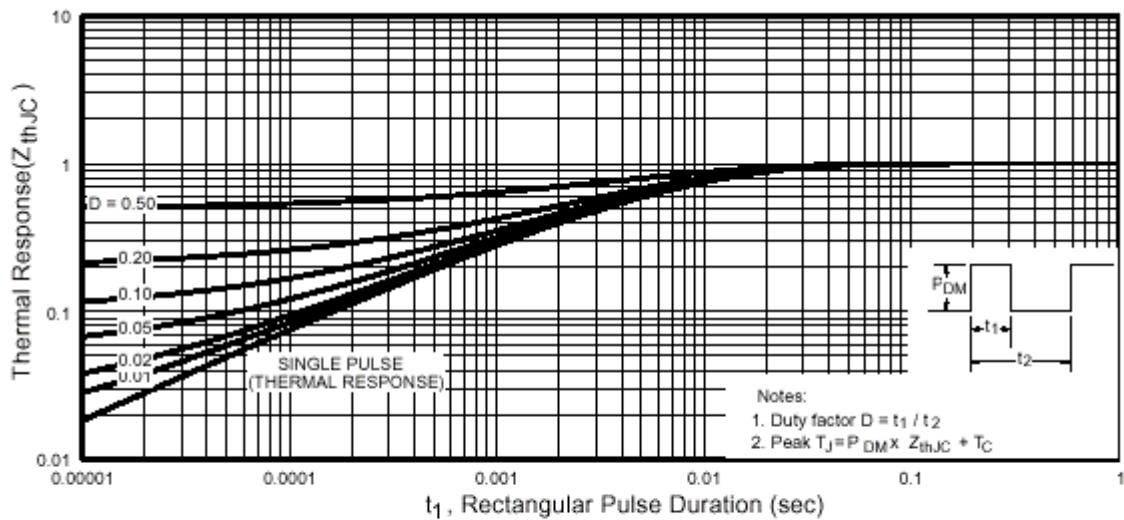


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case